

## Silicon PNP Darlington Power Transistor

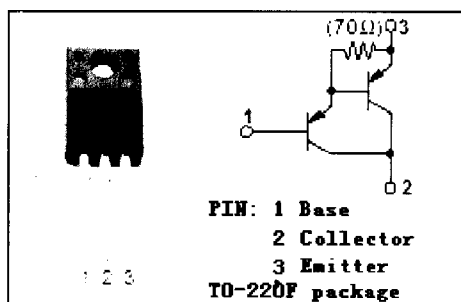
## 2SB1626

### DESCRIPTION

- High DC Current Gain
- Low-Collector Saturation Voltage
- Complement to Type 2SD2495

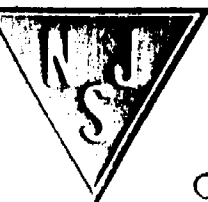
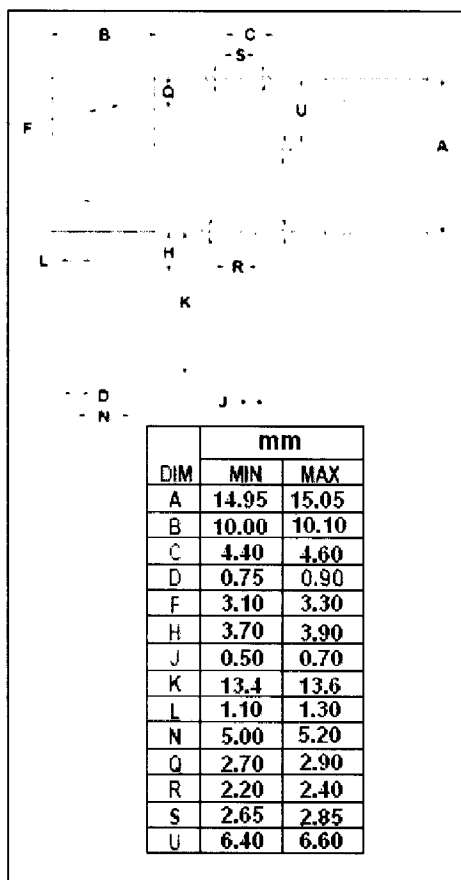
### APPLICATIONS

- Designed for audio, series regulator and general purpose applications.



### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-110	V
$V_{CEO}$	Collector-Emitter Voltage	-110	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-6	A
$I_B$	Base Current- Continuous	-1	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-110			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -5\text{mA}$			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -5\text{mA}$			-3.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -110\text{V}; I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	5000		30000	
$C_{OB}$	Collector Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		110		pF
$f_T$	Current-Gain—Bandwidth Product	$I_E = 0.5\text{A}; V_{CE} = -12\text{V}$		100		MHz

#### ◆ $h_{FE}$ Classifications

O	P	Y
5000-12000	6500-20000	15000-30000